

1st workshop on

Compound Semiconductor Technology for Advanced Electronic Devices

Chalmers University of Technology

and

Kyungpook National University

Thursday –Friday April 21st – 22nd 2016

Chalmers, Department of Microtechnology and Nanoscience – MC2



The workshop is open to everyone. If you wish to join, please contact Jan Grahn (jan.grahn@chalmers.se)

Workshop program

Thursday April 21st Room A810 Luftbryggan floor 8 at MC2

1200	Arrival at MC2 entrance, Kemivägen 9	
	Welcome to Chalmers and MC2	Jan Grahn
Lunch 1230	Restaurant Hyllan	
1330-1400	KNU's III-V programs	Dae-Hyun Kim
1400-1430	Chalmers' research on III-V electronic devices	Jan Grahn
1430-1450	Fabrication and Characterization of GaN-based Vertical Nanowire FETs	Young-Woo Cho
Coffee break		
1510-1530	InP HEMTs with noise temperature below 1 K	Eunjung Cha
1530-1550	Development of InGaAs-based TFETs	Ji Min Baek

1550-1610 Off-state in AlGaIn/GaN HFET with TMAH Surface Treatment Won-Sang Park

Tour Nanofabrication Laboratory at MC2

1745 Dinner (TBA). MC2 entrance.

Friday April 22nd Coffee Room D6 at floor 6, MC2

0900-0920 InP HEMT technology for cryogenic LNAs Per-Åke Nilsson

0920-0940 Improvement of interface-state density (D_{it}) in high-k/InGaAs MOSCAPs
by High-Pressure-Annealing (HPA) Jin Su Kim

0940-1000 Cryogenic low-noise amplifiers Niklas Wadefalk

Coffee break

1020-1040 High performance InGaAs MOSFETs with Al_2O_3/HfO_2 Seung-Woo Son

1040-1100 Towards InP HEMTs with superconducting gate Arsalan Pourkabirian

1100-1120 Universal mobility behavior in InGaAs MOSFETs Jung Ho Park

Tour THz measurement laboratory at MC2, Chalmers

Lunch 1200 (TBA), End workshop

Registered participants

Chalmers

Jan Grahn

Per-Åke Nilsson

Arsalan Pourkabirian

Eunjung Cha

Bengt Nilsson

Piotr Starski

Kyungpook National University

Dae-Hyun Kim

Young-Woo Cho

Ji Min Baek

Won-Sang Park

Jin Su Kim

Seung-Woo Son

Jung Ho Park

Low Noise Factory AB

Niklas Wadefalk

Giuseppe Moschetti